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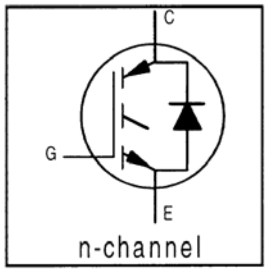
International
IOR Rectifier

IRG4PSC71UDPbF

UltraFast CoPack IGBT

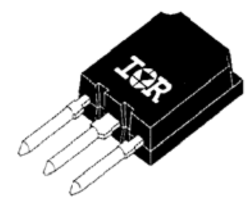
INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE



$V_{CES} = 600V$

$V_{CE(on)\ typ.} = 1.67V$

$@V_{GE} = 15V, I_C = 60A$



SUPER - 247

Features

- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency (minimum switching and conduction losses) than prior generations
- IGBT co-packaged with HEXFRED ultrafast, ultrasoft recovery anti-parallel diodes for use in bridge configurations
- Industry-benchmark Super-247 package with higher power handling capability compared to same footprint TO-247
- Creepage distance increased to 5.35mm
- Lead-Free

Benefits

- Generation 4 IGBT's offer highest efficiencies available
- Maximum power density, twice the power handling of TO-247, less space than TO-264
- IGBTs optimized for specific application conditions
- HEXFRED diodes optimized for performance with IGBTs
- Cost and space saving in designs that require multiple, paralleled IGBTs

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
I_C @ T_C = 25°C	Continuous Collector Current	85⑤	A
I_C @ T_C = 100°C	Continuous Collector Current	60	
I_{CM}	Pulsed Collector Current ①	200	
I_{LM}	Clamped Inductive Load Current ②	200	
I_F @ T_C = 100°C	Diode Continuous Forward Current	60	
I_{FM}	Diode Maximum Forward Current	350	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
P_D @ T_C = 25°C	Maximum Power Dissipation	350	W
P_D @ T_C = 100°C	Maximum Power Dissipation	140	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	

Thermal Resistance\ Mechanical

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	——	——	0.36	°C/W
$R_{\theta JC}$	Junction-to-Case - Diode	——	——	0.69	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	——	0.24	——	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	——	——	38	
	Recommended Clip Force	20.0(2.0)	——	——	N (kgf)
	Weight	——	6 (0.21)	——	g (oz)

09/13/04

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage③	600	—	—	V	V_{GE} = 0V, I_C = 250μA	
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.39	—	V/°C	V_{GE} = 0V, I_C = 10mA	
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.67	2.0	V	I_C = 60A	V_{GE} = 15V
		—	1.95	—		I_C = 100A	See Fig. 2, 5
		—	1.71	—		I_C = 60A, T_J = 150°C	
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		V_{CE} = V_{GE}, I_C = 250μA	
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-13	—	mV/°C	V_{CE} = V_{GE}, I_C = 1.5mA	
g_{fe}	Forward Transconductance ④	47	70	—	S	V_{CE} = 50V, I_C = 60A	
I_{CES}	Zero Gate Voltage Collector Current	—	—	500	μA	V_{GE} = 0V, V_{CE} = 600V	
		—	—	13	mA	V_{GE} = 0V, V_{CE} = 600V, T_J = 150°C	
V_{FM}	Diode Forward Voltage Drop	—	1.4	1.7	V	I_C = 60A	See Fig. 13
		—	1.3	—		I_C = 60A, T_J = 150°C	
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V_{GE} = ±20V	

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	
Q_g	Total Gate Charge (turn-on)	—	340	520	nC	I_C = 60A	
Qge	Gate - Emitter Charge (turn-on)	—	44	66		V_{CC} = 400V See Fig. 8	
Q_{gc}	Gate - Collector Charge (turn-on)	—	160	240		V_{GE} = 15V	
$t_{d(on)}$	Turn-On Delay Time	—	90	—	ns	T_J = 25°C	
t_r	Rise Time	—	94	—		I_C = 60A, V_{CC} = 480V	
$t_{d(off)}$	Turn-Off Delay Time	—	245	368		V_{GE} = 15V, R_G = 5.0Ω	
t_f	Fall Time	—	110	167		Energy losses include "tail" and	
E_{on}	Turn-On Switching Loss	—	3.26	—	mJ	diode reverse recovery.	
E_{off}	Turn-Off Switching Loss	—	2.27	—		See Fig. 9, 10, 11, 18	
E_{ts}	Total Switching Loss	—	5.53	7.2			
$t_{d(on)}$	Turn-On Delay Time	—	91	—	ns	T_J = 150°C, See Fig. 9, 10, 11, 18	
t_r	Rise Time	—	88	—		I_C = 60A, V_{CC} = 480V	
$t_{d(off)}$	Turn-Off Delay Time	—	353	—		V_{GE} = 15V, R_G = 5.0Ω	
t_f	Fall Time	—	150	—		Energy losses include "tail" and	
E_{ts}	Total Switching Loss	—	7.1	—	mJ	diode reverse recovery.	
L_E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package	
C_{ies}	Input Capacitance	—	7500	—	pF	V_{GE} = 0V	
C_{oes}	Output Capacitance	—	720	—		V_{CC} = 30V See Fig. 7	
C_{res}	Reverse Transfer Capacitance	—	93	—		f = 1.0MHz	
t_{rr}	Diode Reverse Recovery Time	—	82	120	ns	T_J = 25°C See Fig.	
		—	140	210		T_J = 125°C 14	I_F = 60A
I_{rr}	Diode Peak Reverse Recovery Current	—	8.2	12	A	T_J = 25°C See Fig.	
		—	13	20		T_J = 125°C 15	V_R = 200V
Q_{rr}	Diode Reverse Recovery Charge	—	364	546	nC	T_J = 25°C See Fig.	
		—	1084	1625		T_J = 125°C 16	di/dt = 200A/μs
$di_{(rec)M}/dt$ During t_b	Diode Peak Rate of Fall of Recovery	—	328	—	A/μs	T_J = 25°C See Fig.	
		—	266	—		T_J = 125°C 17	

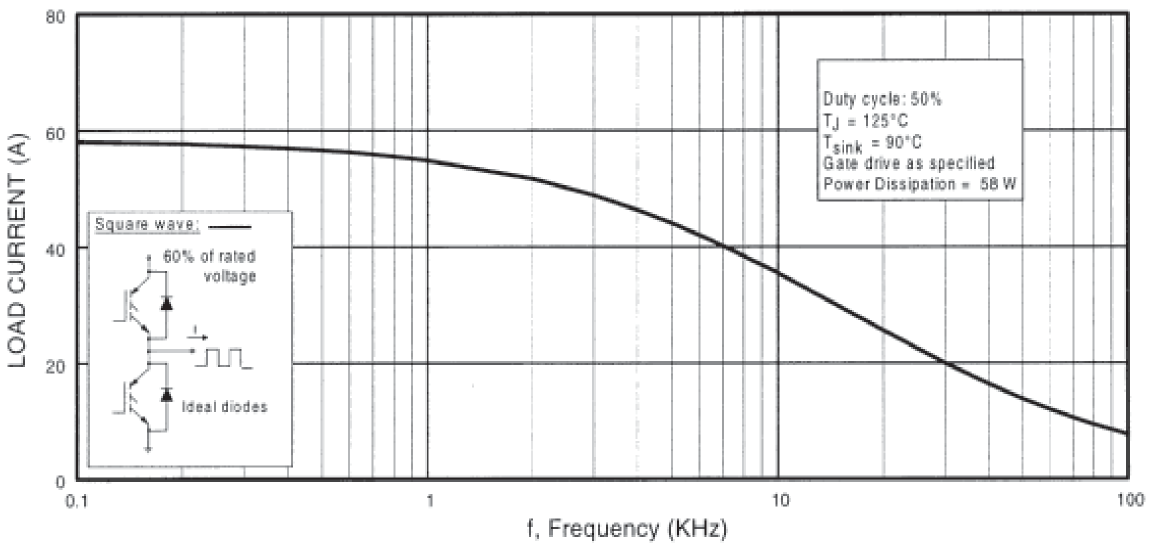


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

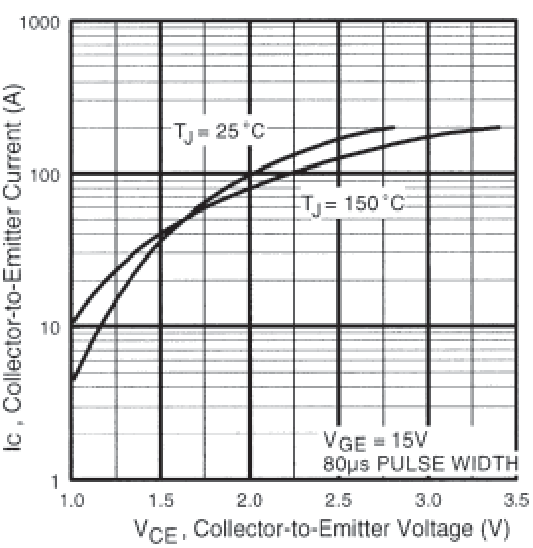


Fig. 2 - Typical Output Characteristics

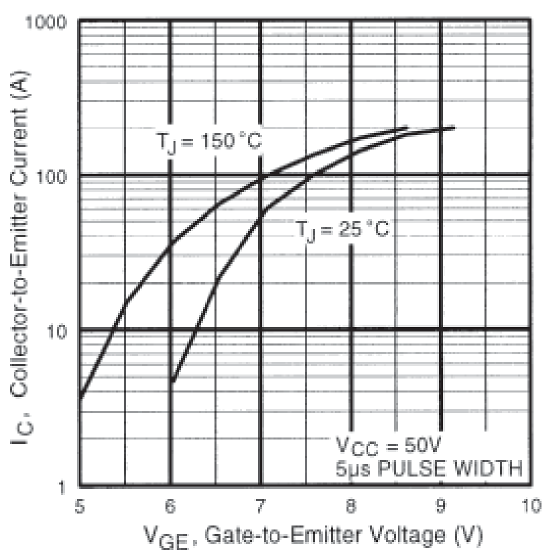


Fig. 3 - Typical Transfer Characteristics

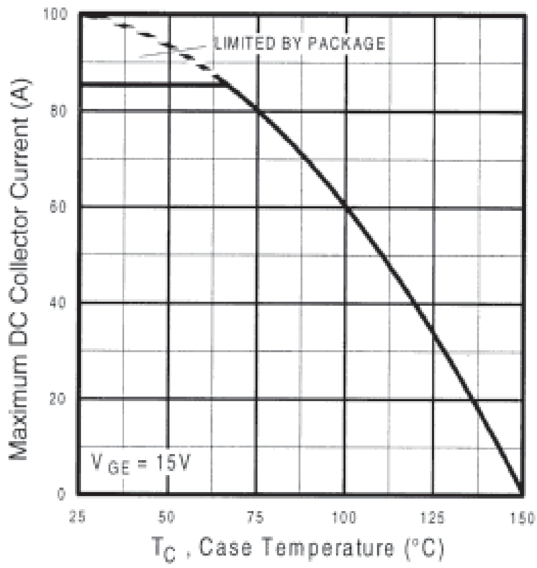


Fig. 4 - Maximum Collector Current vs. Case Temperature

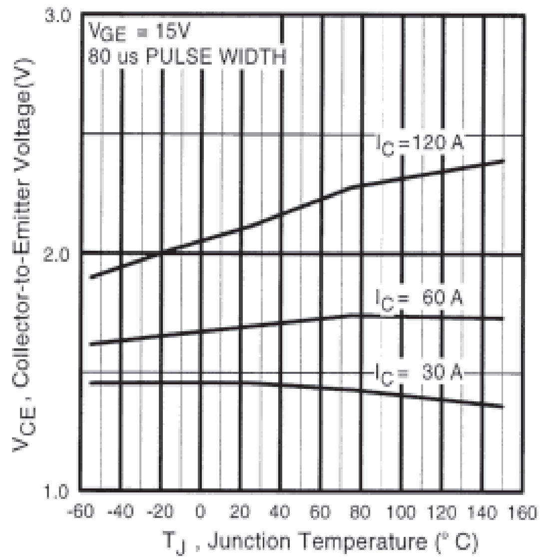


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

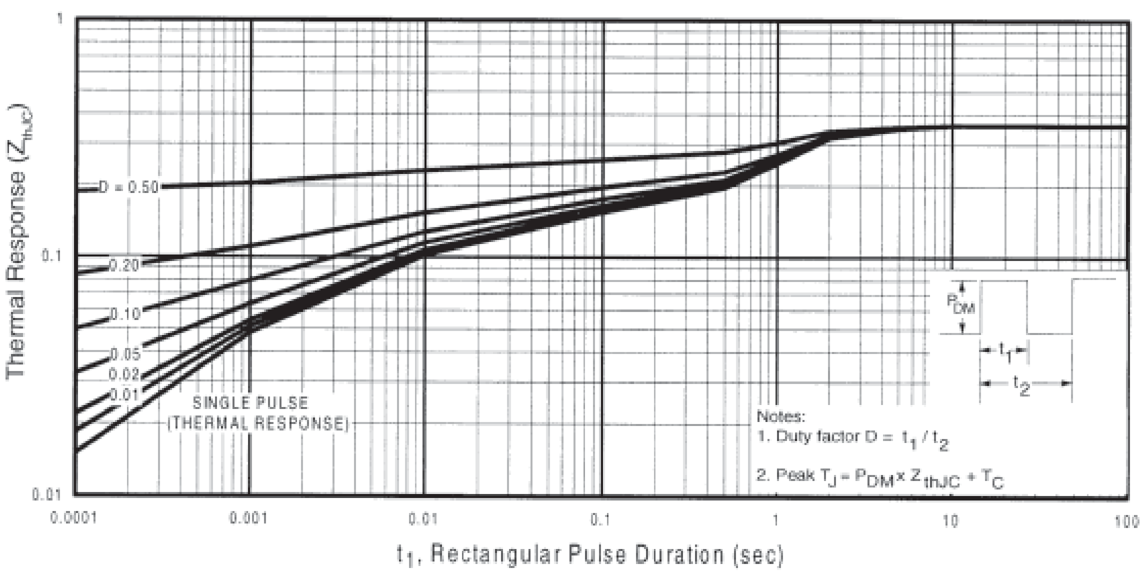


Fig. 6 - Maximum IGBT Effective Transient Thermal Impedance, Junction-to-Case

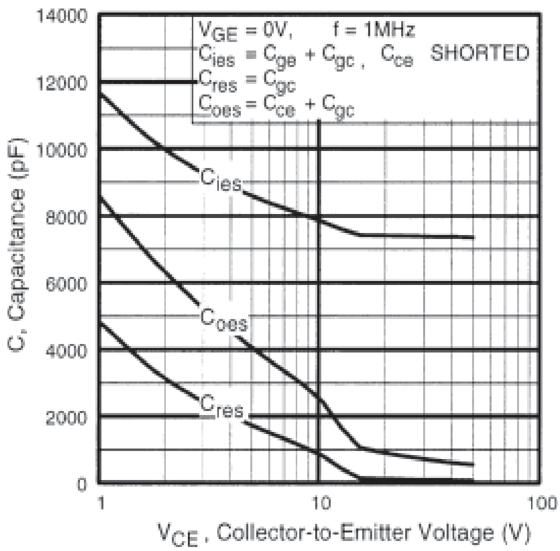


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

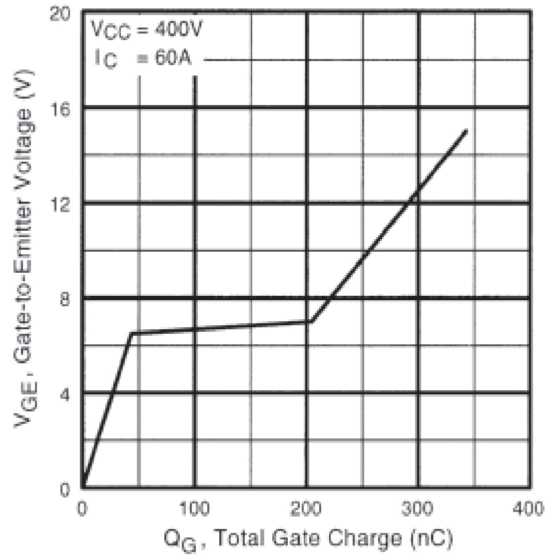


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

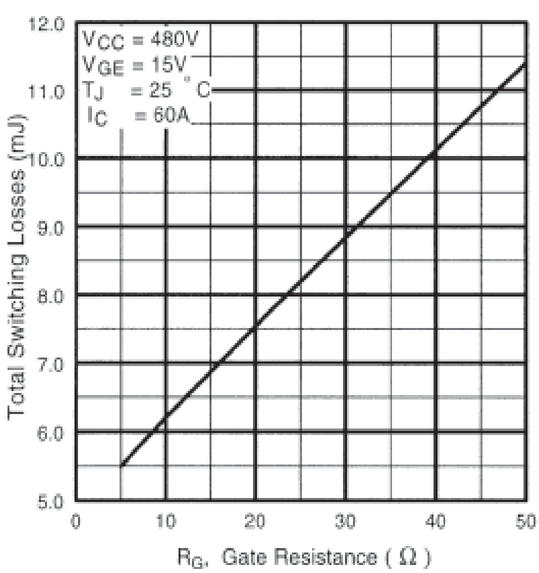


Fig. 9 - Typical Switching Losses vs. Gate Resistance

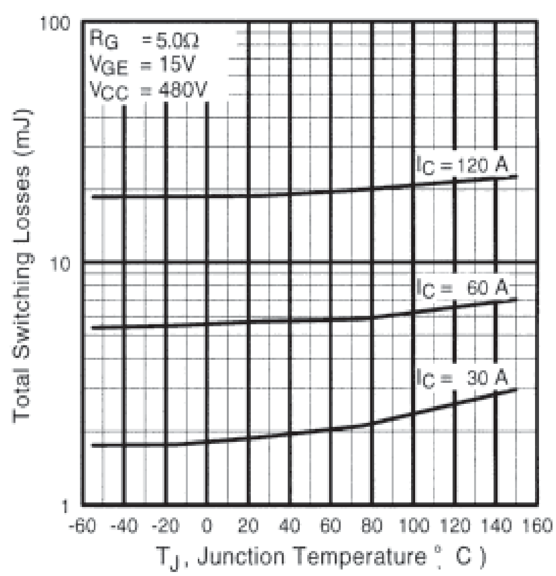


Fig. 10 - Typical Switching Losses vs. Junction Temperature

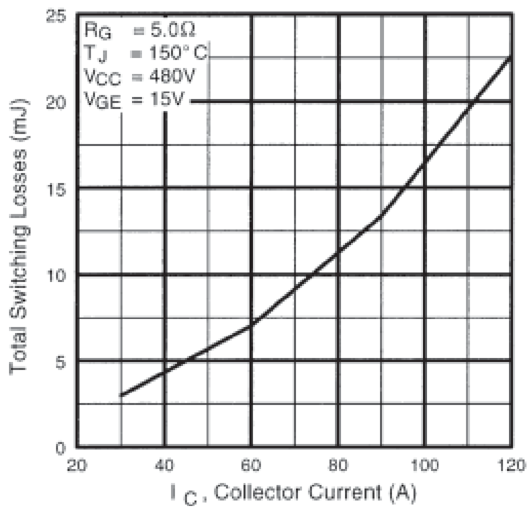


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

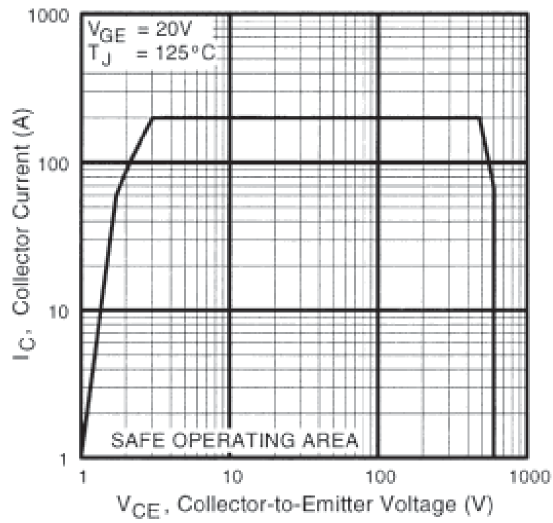


Fig. 12 - Turn-Off SOA

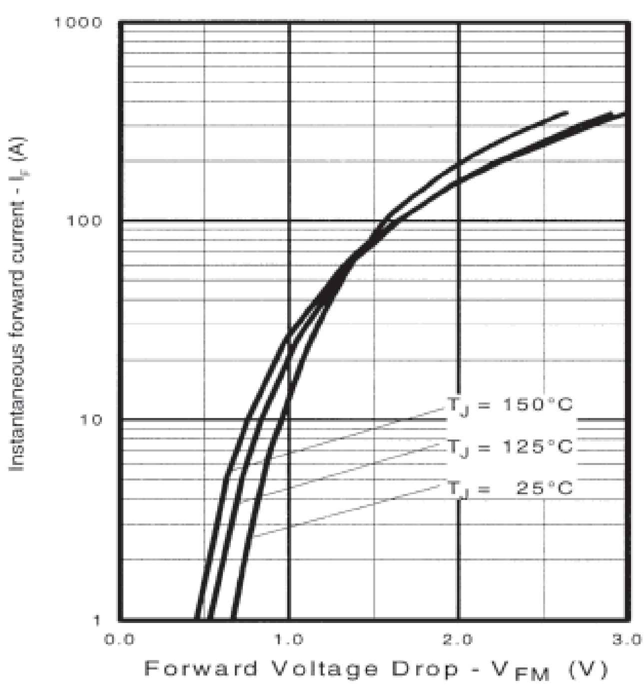


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

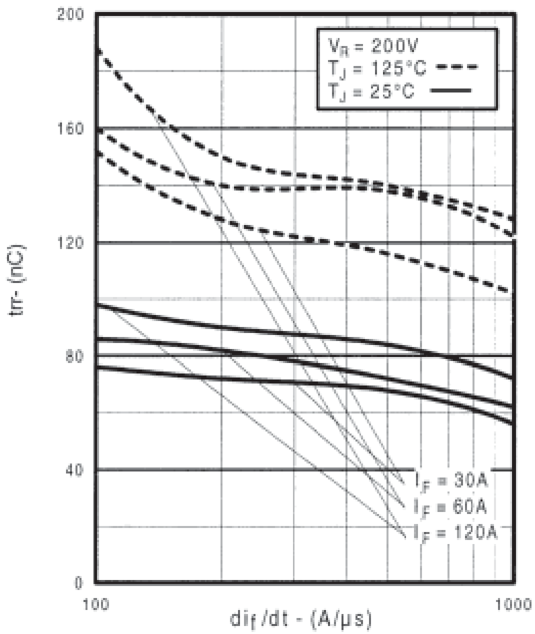


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

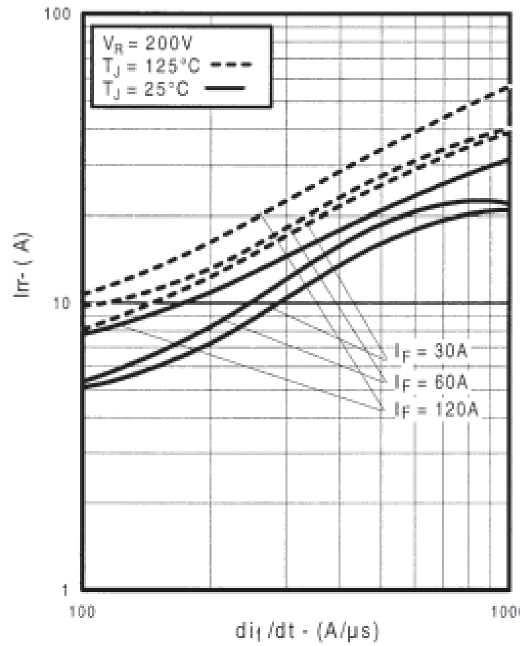


Fig. 15 - Typical Recovery Current vs. di_f/dt

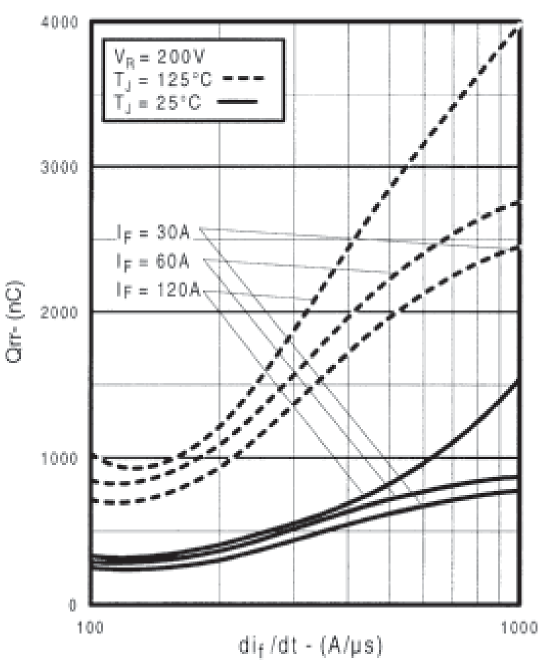


Fig. 16 - Typical Stored Charge vs. di_f/dt

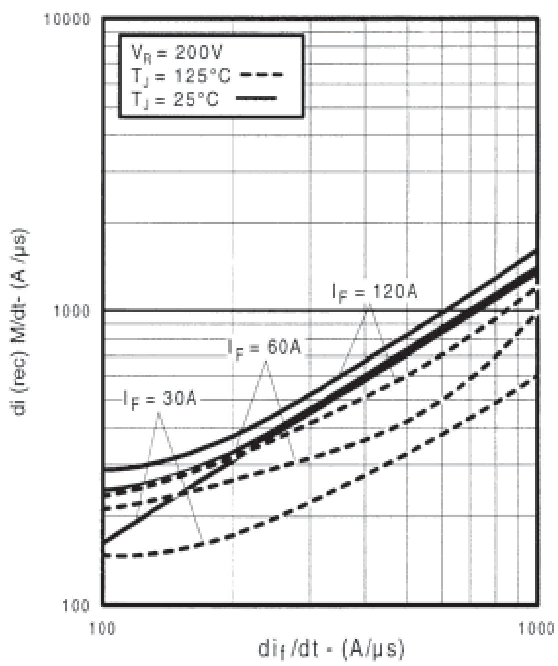


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

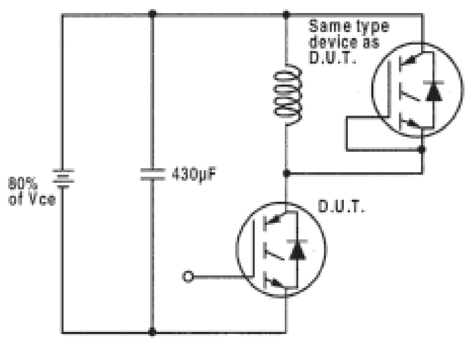


Fig. 18a - Test Circuit for Measurement of I_{LM}, E_{on}, $E_{off(diode)}$, t_{rr}, Q_{rr}, I_{rr}, $t_{d(on)}$, t_r, $t_{d(off)}$, t_f

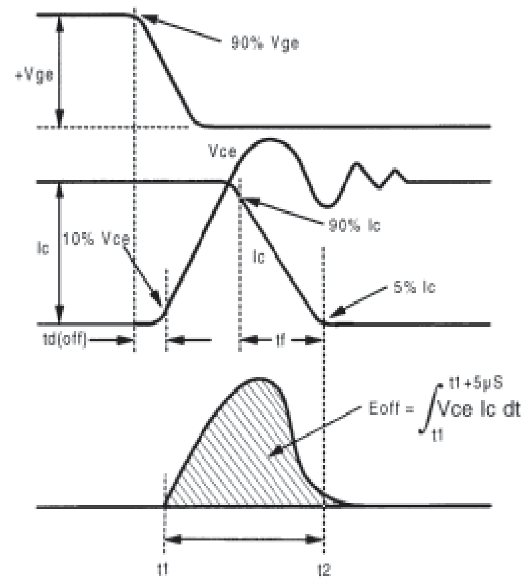


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off}, $t_{d(off)}$, t_f

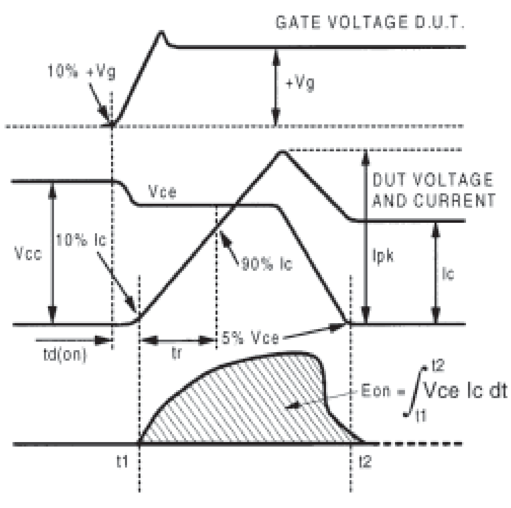


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on}, $t_{d(on)}$, t_r

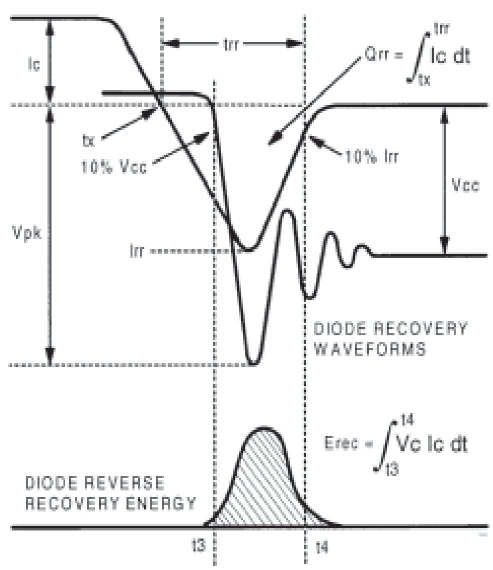


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec}, t_{rr}, Q_{rr}, I_{rr}

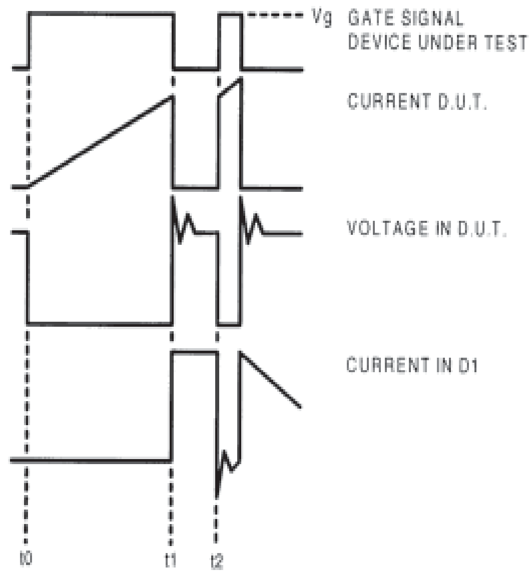


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

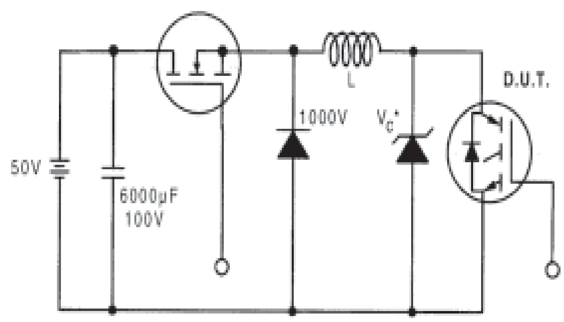


Figure 19. Clamped Inductive Load Test Circuit

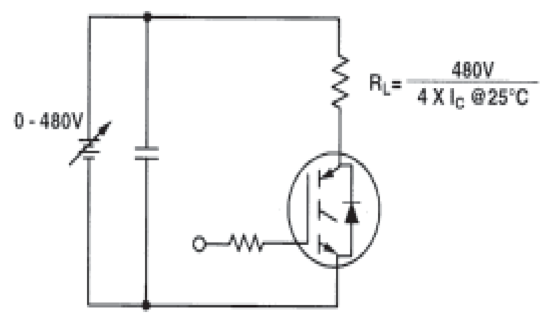


Figure 20. Pulsed Collector Current Test Circuit

Notes:

① Repetitive rating: V_{GE}=20V; pulse width limited by maximum junction temperature (figure 20)

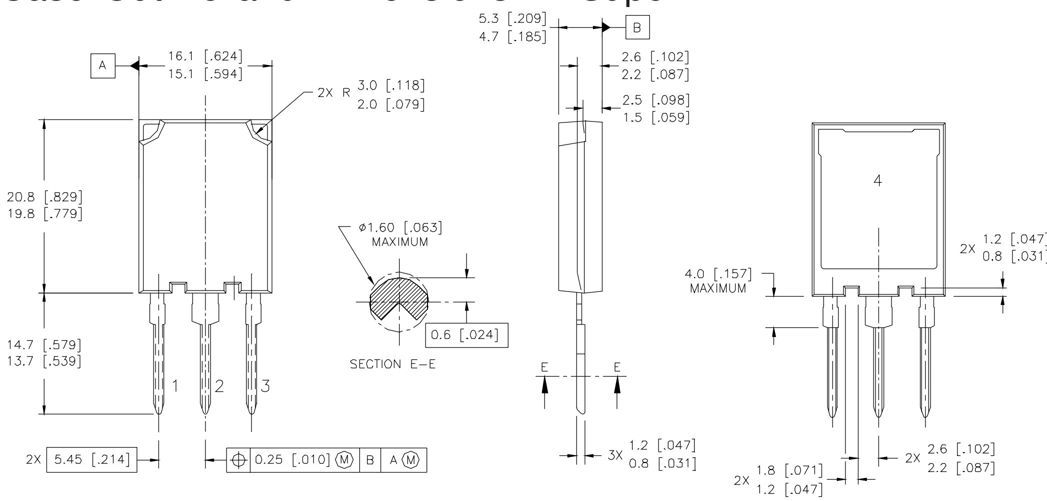
② V_{CC}=80%(V_{CES}), V_{GE}=20V, L=10µH, R_G= 5.0Ω (figure 19)

③ Pulse width ≤ 80µs; duty factor ≤ 0.1%

④ Pulse width 5.0µs, single shot

⑤ Current limited by the package, (Die current = 100A)

Case Outline and Dimensions — Super-247



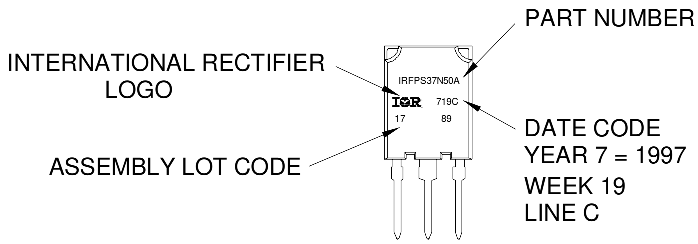
NOTES:
1. DIMENSIONS & TOLERANCING PER ASME Y14.5M-1994
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETRES [INCHES]

LEAD ASSIGNMENTS

MOSFET	IGBT
1 - GATE	1 - GATE
2 - DRAIN	2 - COLLECTOR
3 - SOURCE	3 - EMITTER
4 - DRAIN	4 - COLLECTOR

Super-247 (TO-274AA) Part Marking Information

EXAMPLE: THIS IS AN IRFPS37N50A WITH
ASSEMBLY LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"



Note: "P" in assembly line position
indicates "Lead-Free"

TOP

Data and specifications subject to change without notice.

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